

# New Jersey Semi-Conductor Products, Inc.

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## BTW67 and BTW69 Series

STANDARD

50A SCRs

### MAIN FEATURES:

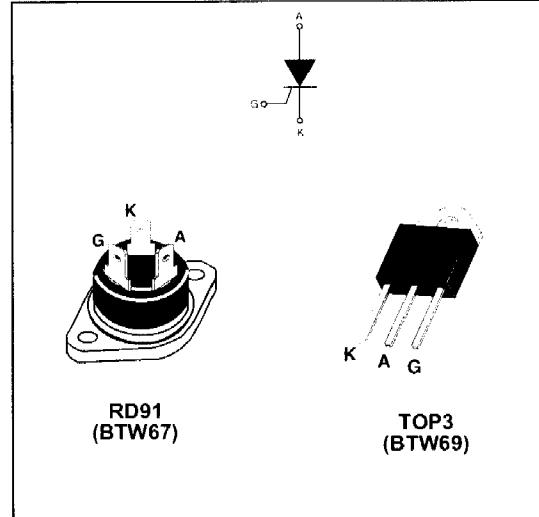
Symbol	Value	Unit
$I_{T(RMS)}$	50	A
$V_{DRM}/V_{RRM}$	600 to 1200	V
$I_{GT}$	80	mA

### DESCRIPTION

Available in high power packages, the BTW67 / BTW69 Series is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment, high power motor control.

Based on a clip assembly technology, they offer a superior performance in surge current handling capabilities.

Thanks to their internal ceramic pad, they provide high voltage insulation (2500V RMS), complying with UL standards



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	RD91	$T_c = 70^\circ C$	50	A
		TOP3 Ins.	$T_c = 75^\circ C$		
$I_{T(AV)}$	Average on-state current (180° conduction angle)	RD91	$T_c = 70^\circ C$	32	A
		TOP3 Ins.	$T_c = 75^\circ C$		
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	$T_j = 25^\circ C$	610	A
		$t_p = 10 \text{ ms}$		580	
$I^2t$	$I^2t$ Value for fusing		$T_j = 25^\circ C$	1680	$A^2s$
$dI/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^\circ C$	50	$A/\mu s$
$I_{GM}$	Peak gate current	$t_p = 20 \mu s$	$T_j = 125^\circ C$	8	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ C$	1	W
$T_{stg}$ $T_j$	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^\circ C$
$V_{RGM}$	Maximum peak reverse gate voltage			5	V

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Quality Semi-Conductors

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## BTW67 and BTW69 Series

ELECTRICAL CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Test Conditions			Value	Unit
$I_{GT}$	$V_D = 12 \text{ V}$ $R_L = 33 \Omega$	MIN.	8	mA	
$V_{GT}$		MAX.	80		
$V_{GD}$		MAX.	1.3		
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN.	0.2	V
$I_H$	$I_T = 500 \text{ mA}$ Gate open		MAX.	150	mA
$I_L$	$I_G = 1.2 I_{GT}$		MAX.	200	mA
$dV/dt$	$V_D = 67\% V_{DRM}$ Gate open	$T_j = 125^\circ\text{C}$	MIN.	1000	$\text{V}/\mu\text{s}$
$V_{TM}$	$I_{TM} = 100 \text{ A}$ $t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.9	V
$V_{t0}$	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	1.0	V
$R_d$	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	8.5	$\text{m}\Omega$
$I_{DRM}$	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	10	$\mu\text{A}$
$I_{RRM}$		$T_j = 125^\circ\text{C}$		5	mA

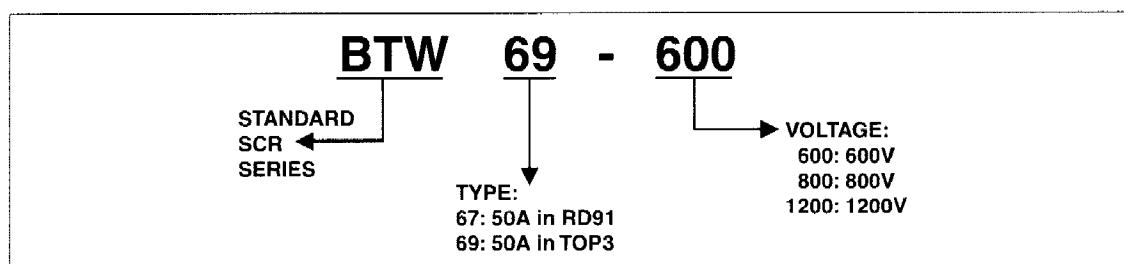
## THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case (DC)		RD91 (Insulated)	1.0	$^\circ\text{C}/\text{W}$
			TOP3 Insulated	0.9	
$R_{th(j-a)}$	Junction to ambient		TOP3 Insulated	50	$^\circ\text{C}/\text{W}$

## PRODUCT SELECTOR

Part Number	Voltage (xxx)			Sensitivity	Package
	600 V	800 V	1200 V		
BTW67-xxx	X	X	X	80 mA	RD91
BTW69-xxx	X	X	X	80 mA	TOP3 Ins.

## ORDERING INFORMATION



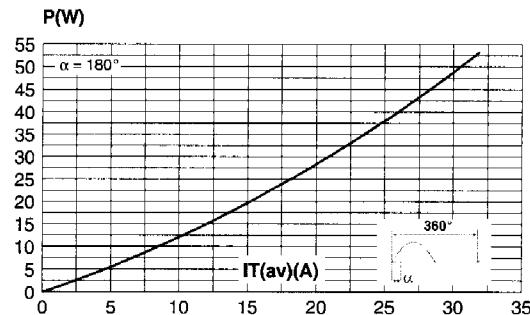
## OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing mode
BTW67-xxx	BTW67xxx	20.0 g	25	Bulk
BTW69-xxx	BTW69xxx	4.5 g	120	Bulk

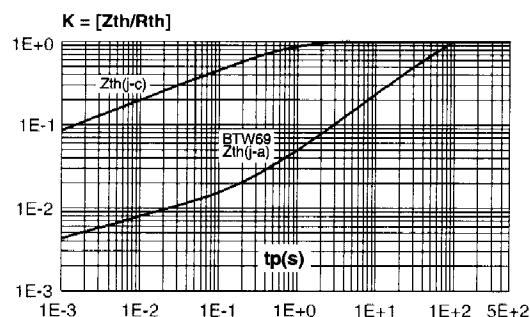
Note: xxx = voltage

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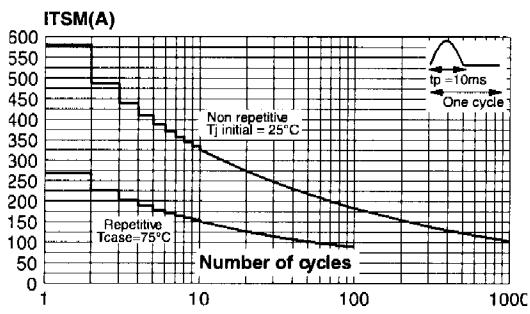
**Fig. 1:** Maximum average power dissipation versus average on-state current.



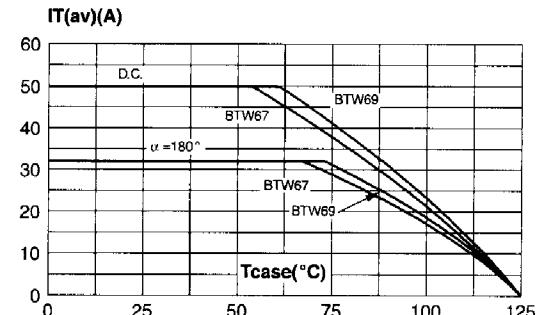
**Fig. 3:** Relative variation of thermal impedance versus pulse duration.



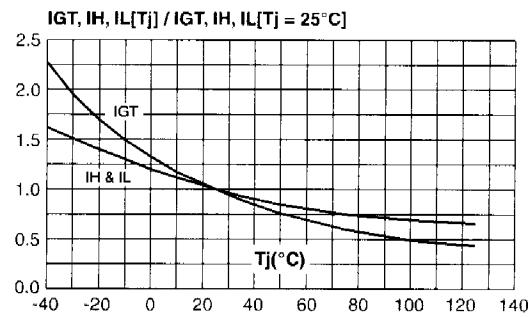
**Fig. 5:** Surge peak on-state current versus number of cycles.



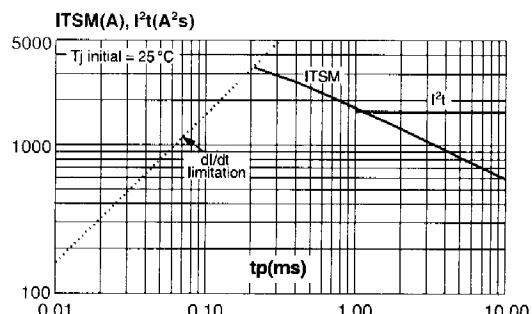
**Fig. 2:** Average and D.C. on-state current versus case temperature.



**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature.

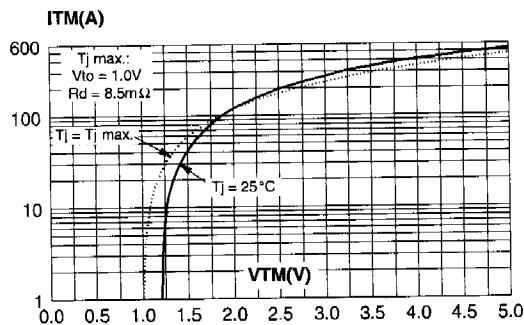


**Fig. 6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $tp < 10ms$ , and corresponding value of  $I^2t$ .



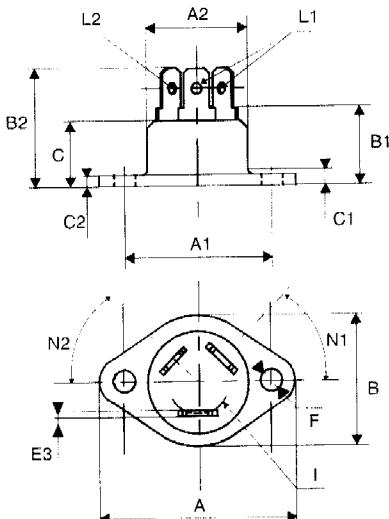
## BTW67 and BTW69 Series

**Fig. 7:** On-state characteristics (maximum values).



### PACKAGE MECHANICAL DATA

RD91 (Plastic)



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A		40.00		1.575
A1	29.90	30.30	1.177	1.193
A2		22.00		0.867
B		27.00		1.063
B1	13.50	16.50	0.531	0.650
B2		24.00		0.945
C		14.00		0.551
C1		3.50		0.138
C2	1.95	3.00	0.077	0.118
E3	0.70	0.90	0.027	0.035
F	4.00	4.50	0.157	0.177
I	11.20	13.60	0.441	0.535
L1	3.10	3.50	0.122	0.138
L2	1.70	1.90	0.067	0.075
N1	33°	43°	33°	43°
N2	28°	38°	28°	38°